

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

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By: Glatzel et al.

For: Semiconductor Component
and Electrochemical Method of Its Manufacture

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11 October 2005

Hon.
Commissioner for Patents
P.O. Box 1450
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Mail Stop PCT**Preliminary Amendment Prior to Claims Fee Calculation**

Sir:

With a view to avoiding excess claims fees otherwise due and to placing the English translation of their subject International Patent Application into a condition believed to satisfy formal aspects of current American patent prosecution practice, Applicants courteously request entry of the following amendment.

In the Specification:

Page 1, lines 5-7: cancel and substitute –Method of Fabricating a Nano-Scaled Semiconductor and Semiconductor Fabricated by the Method–;

line 9: cancel “Specification” and substitute therefor
–BACKGROUND OF THE INVENTION.

1. Field of the Invention.–;

line 22: insert –2. The Prior Art.–;

Page 4, line 7: insert –OBJECT OF THE INVENTION.–;

line 18: insert –SUMMARY OF THE INVENTION.–;